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Atty. Dkt. 28953.2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Makoto IWAI et al

Serial No. (new)

Based on PCT/JP2005/006692

Int'l Filing Date: March 30, 2005

For: GALLIUM NITRIDE SINGLE CRYSTAL GROWING METHOD  
AND GALLIUM NITRIDE SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Customer Window  
U.S. Patent & Trademark Office  
Randolph Building  
401 Dulany Street  
Alexandria, VA 22314

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO-1449. A copy of the foreign references listed on Form PTO-1449 is attached.

Refs. AE-AG are cited in the International Search Report, copy attached. References AP, AC and AD are discussed at page 1 of the specification. U.S. Patent No. 6,398,867 (Ref. AB) corresponds to Japanese Patent Publication 2003-511326 (AE).

The above information is presented so that the Patent and Trademark Office may, in the first instance, determine any materiality thereof to the claimed invention. See 37 C.F.R. 1.104(a) and 1.106(b) concerning the PTO duty to consider and use any such information. It is respectfully

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requested that the information be expressly considered during the prosecution of this application, and that these references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Respectfully submitted,

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Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 28953.2004	Application No. New - unassigned	
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))		Applicant		10/594846 Makoto IWAI et al		
		Filing Date Herewith		Group Art Unit		

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	6,949,140	9/2005	Sarayama et al	117	81	
	AB	6,398,867	6/2002	D'Evelyn et al	117	11	

**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publn. Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AC	2002-293696	10/2002	Japan			Abstract	
	AD	2003-292400	10/2003	Japan			Abstract	
	AE	2003-511326	3/2003	Japan			X	
	AF	2005-8444	1/2005	Japan			Abstract	
	AG	WO2004/013385	6/2003	WIPO			Abstract	
	AH	WO01/024921	9/2000	WIPO				
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
	AO							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
	AP	Kawamura, F. et al, "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique," Jpn. J. Appl. Phys., Vol. 42 (2003), pp. L4-L6
	AQ	
	AR	
	AS	
	AT	

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	